

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	760	(isolat\$4 adj trench) near3 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:54
L2	1	(anneal\$4 near4 (floating adj gate)) same (water adj vapor adj atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:34
L3	1	(anneal\$4 with (floating adj gate)) same (water adj vapor adj atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:35
L4	77	anneal\$4 same (water adj vapor adj atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:50
L5	2	1 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:49
L8	39	4 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:53
L9	2	8 and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:50
L10	708	1 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:54

L11	204	10 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:55
L12	152	11 and (insulat\$4 adj (film or layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:56
L13	114	@ad <="20030527" and 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:18
L14	95	(non-volatile adj memory adj cell) and (tunnel adj insulat\$4 adj (film or layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 22:25
L15	93	14 and ((floating adj gate) or (gate adj electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 21:59
L16	88	15 and (control adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 22:00
L17	74	@ad <="20030527" and 16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 22:25
L18	680	438/197.ccls.	USPAT	OR	OFF	2005/09/24 23:18
L19	5	18 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 22:36
L20	1313	438/257.ccls.	USPAT	OR	OFF	2005/09/24 23:20
L21	131	20 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 22:55
L22	113	@ad <="20030527" and 21	USPAT	OR	OFF	2005/09/24 22:55
L23	415	438/259.ccls.	USPAT	OR	OFF	2005/09/24 23:22

L24	30	23 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 22:58
L25	25	@ad <="20030527" and 24	USPAT	OR	OFF	2005/09/24 22:58
L26	636	438/264.ccls.	USPAT	OR	OFF	2005/09/24 22:58
L27	47	26 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 23:16
L28	46	@ad <="20030527" and 27	USPAT	OR	OFF	2005/09/24 23:16
L29	266	438/294.ccls.	USPAT	OR	OFF	2005/09/24 23:16
L30	4	29 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 23:19
L31	4	@ad <="20030527" and 30	USPAT	OR	OFF	2005/09/24 23:20
L32	635	438/197.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:18
L34	5	32 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:20
L35	668	438/257.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:20
L36	67	35 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:22
L37	40	@ad <="20030527" and 36	US-PGPUB	OR	OFF	2005/09/24 23:22
L38	127	438/259.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:22
L39	9	38 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:28
L40	5	@ad <="20030527" and 39	US-PGPUB	OR	OFF	2005/09/24 23:22
L41	131	438/264.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:23
L42	8	41 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:30
L43	72	438/294.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:30
L44	1	43 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:30